

Dual N-Ch MOSFET

General Description

The WSP6946 is the highest performance trench N-ch MOSFET with extreme high cell density , which provide excellent $\mathsf{R}_{\mathsf{DSON}}$ and gate charge for most of the synchronous buck converter applications .

The WSP6946 meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

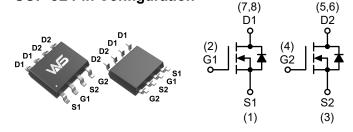
Product Summery

| BV _{DSS} | R _{DSON} | I _D |
|-------------------|-------------------|----------------|
| 60V | 43mΩ | 6.5A |

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOP-8L Pin Configuration



Absolute Maximum Ratings

| Symbol | Parameter | Rating | Units |
|-------------------------------------|--|------------|-------|
| V _{DS} | Drain-Source Voltage | 60 | V |
| V _{GS} | Gate-Source Voltage | ±20 | V |
| I₀@T _C =25℃ | Continuous Drain Current, V _{GS} @ 10V ¹ | 6.5 | А |
| I _D @T _C =70℃ | Continuous Drain Current, V _{GS} @ 10V ¹ | 4.5 | A |
| I _{DM} | Pulsed Drain Current ² | 24 | A |
| EAS | Single Pulse Avalanche Energy ³ | 12 | mJ |
| I _{AS} | Avalanche Current | 16 | A |
| P₀@T _A =25℃ | Total Power Dissipation ⁴ | 2.5 | W |
| T _{STG} | Storage Temperature Range | -55 to 150 | °C |
| TJ | Operating Junction Temperature Range -55 to 150 | | °C |

Thermal Data

| Symbol | Parameter | | Max. | Unit |
|------------------|--|--|------|------|
| R _{eja} | Thermal Resistance Junction-ambient ¹ | | 90 | °C/W |
| R _{eJC} | Thermal Resistance Junction-Case ¹ | | 50 | °C/W |



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Electrical Characteristics (T_J=25 °C, unless otherwise noted)

| Symbol | Parameter | Conditions | Min. | Тур. | Max. | Unit | |
|--------------------------------------|--|--|------------------------------|-------|------|------|--|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V , I _D =250uA | 60 | | | V | |
| $\triangle BV_{DSS} / \triangle T_J$ | BVDSS Temperature Coefficient | Reference to 25 $^\circ\!\mathrm{C}$, I_D=1mA | | 0.044 | | V/℃ | |
| Б | Static Drain-Source On-Resistance ² | V _{GS} =10V , I _D =6.3A | 0V , I _D =6.3A 43 | | 52 | | |
| R _{DS(ON)} | Static Drain-Source On-Resistance | V _{GS} =4.5V , I _D =4A | | 46 | 60 | mΩ | |
| V _{GS(th)} | Gate Threshold Voltage | | 1.0 | 2.0 | 3.0 | V | |
| $	riangle V_{GS(th)}$ | V _{GS(th)} Temperature Coefficient | — V _{GS} =V _{DS} , I _D =250uA | | -4.8 | | mV/℃ | |
| | | V _{DS} =48V , V _{GS} =0V , T _J =25°C | | | 1 | | |
| I _{DSS} | Drain-Source Leakage Current | V_{DS} =48V , V_{GS} =0V , T_{J} =55 $^{\circ}\mathrm{C}$ | | | 5 | uA | |
| I _{GSS} | Gate-Source Leakage Current | $V_{GS}=\pm20V$, $V_{DS}=0V$ | | | ±100 | nA | |
| gfs | Forward Transconductance | V _{DS} =5V , I _D =4A | | 28.3 | | S | |
| R _g | Gate Resistance | V _{DS} =0V , V _{GS} =0V , f=1MHz | | 2.5 | 5 | Ω | |
| Qg | Total Gate Charge (10V) | | | 14 | 20 | | |
| Q _{gs} | Gate-Source Charge | V _{DS} =48V , V _{GS} =10V , I _D =6.3A | | 2.6 | | nC | |
| Q _{gd} | Gate-Drain Charge | | | 2.2 | | | |
| T _{d(on)} | Turn-On Delay Time | | | 6 | 11 | | |
| Tr | Rise Time | V_{DD} =30V , V_{GEN} =10V , R_{G} =6 Ω | | 8 | 15 | | |
| T _{d(off)} | Turn-Off Delay Time | I _D =4A ,RL=30Ω | | 6 | 11 | ns | |
| T _f | Fall Time | | | 23 | 42 | | |
| C _{iss} | Input Capacitance | | | 870 | | | |
| Coss | Output Capacitance | V _{DS} =15V , V _{GS} =0V , f=1MHz | | 70 | | pF | |
| C _{rss} | Reverse Transfer Capacitance | | | 35 | | | |

Guaranteed Avalanche Characteristics

| Symbol | Parameter | Conditions | Min. | Тур. | Max. | Unit |
|--------|------------------------------------|--|------|------|------|------|
| EAS | Single Pulse Avalanche Energy 5 | V_{DD} =25V , L=0.1mH , I _{AS} =12A | 10 | | | mJ |

Diode Characteristics

| Symbol | Parameter | Conditions | Min. | Тур. | Max. | Unit |
|-----------------|--|--|------|------|------|------|
| Is | Continuous Source Current ^{1,6} | | | | 2.5 | А |
| I _{SM} | Pulsed Source Current ^{2,6} | $V_G = V_D = 0V$, Force Current | | | 24 | А |
| V _{SD} | Diode Forward Voltage ² | V _{GS} =0V , I _S =1A , T _J =25℃ | | | 1.1 | V |
| trr | Reverse Recovery Time | | | 20 | | nS |
| Q _{rr} | Reverse Recovery Charge | l⊧=6.3A , dl/dt=100A/μs , Tյ=25℃ | | 18 | | nC |

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec.

2.The data tested by pulsed , pulse width $\,\leq\,$ 300us , duty cycle $\,\leq\,$ 2%

3. The EAS data shows Max. rating . The test condition is $V_{\text{DD}}\text{=}25\text{V}, V_{\text{GS}}\text{=}10\text{V}, \text{L=}0.1\text{mH}, \text{I}_{\text{AS}}\text{=}12\text{A}$

4.The power dissipation is limited by 150 $^\circ\!\mathrm{C}$ junction temperature

5.The Min. value is 100% EAS tested guarantee.

6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



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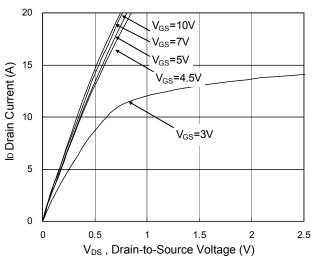
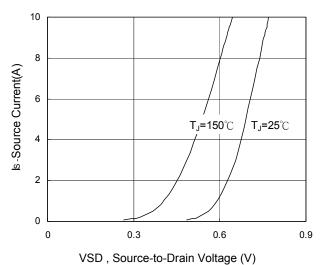
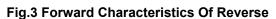
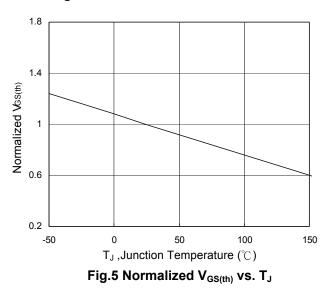


Fig.1 Typical Output Characteristics







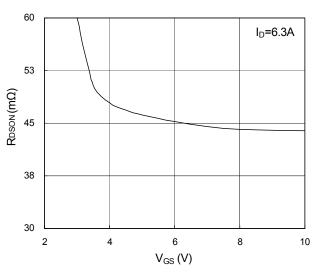


Fig.2 On-Resistance vs. Gate-Source

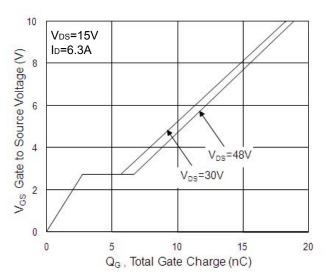
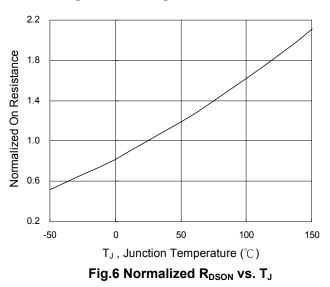
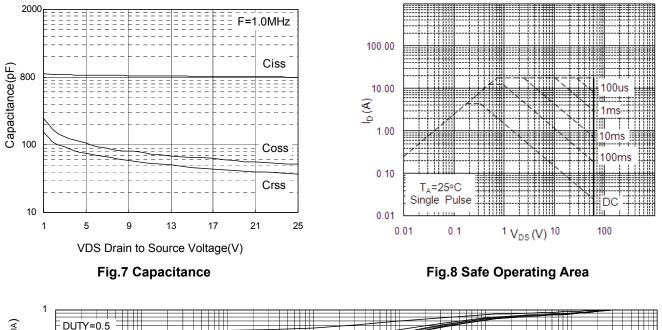


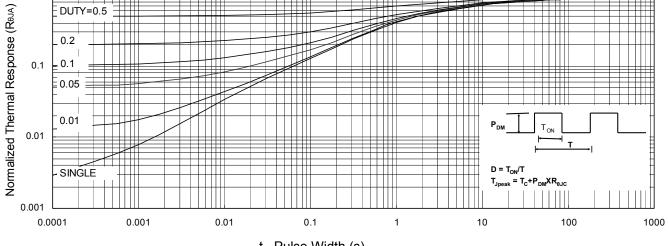
Fig.4 Gate-Charge Characteristics





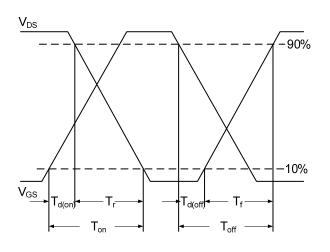
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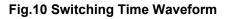




t , Pulse Width (s)







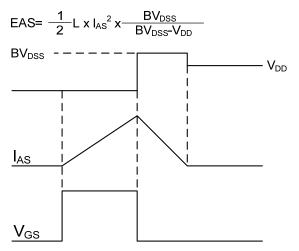
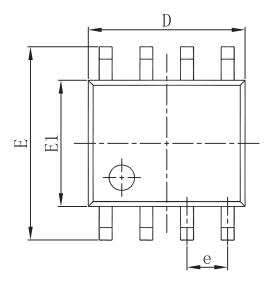
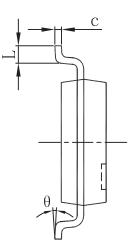


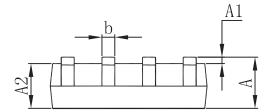
Fig.11 Unclamped Inductive Switching Waveform



Packaging information







| Symbol | Dimensions In Millimeters | | Dimensions | In Inches |
|--------|---------------------------|-------|-------------|-----------|
| | Min | Max | Min | Max |
| А | 1.350 | 1.750 | 0.053 | 0.069 |
| A1 | 0.100 | 0.250 | 0.004 | 0.010 |
| A2 | 1.350 | 1.550 | 0.053 | 0.061 |
| b | 0.330 | 0.510 | 0.013 | 0.020 |
| с | 0.170 | 0.250 | 0.007 | 0.010 |
| D | 4.800 | 5.000 | 0.189 | 0. 197 |
| e | 1.270 (BSC) | | 0.050 (BSC) | |
| Е | 5.800 | 6.200 | 0.228 | 0.244 |
| E1 | 3.800 | 4.000 | 0.150 | 0.157 |
| L | 0.400 | 1.270 | 0.016 | 0.050 |
| θ | 0 ° | 8° | 0° | 8° |



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